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Schubert et al.(10) **Pub. No.: US 2016/0284996 A1**(43) **Pub. Date: Sep. 29, 2016**(54) **MEMORY CELLS AND METHODS OF FORMING MEMORY CELLS**

2015, now Pat. No. 9,257,646, which is a division of application No. 14/070,407, filed on Nov. 1, 2013, now Pat. No. 8,981,334.

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(57) **ABSTRACT**

Some embodiments include a memory cell having a first electrode, and an intermediate material over and directly against the first electrode. The intermediate material includes stabilizing species corresponding to one or both of carbon and boron. The memory cell also has a switching material over and directly against the intermediate material, an ion reservoir material over the switching material, and a second electrode over the ion reservoir material. Some embodiments include methods of forming memory cells.

